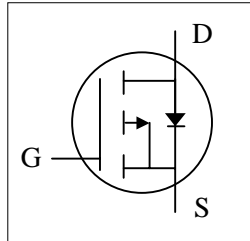
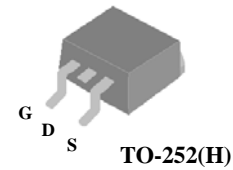




- ▼ 100% UIS Test
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	-30V
$R_{DS(ON)}$	20m $\Omega$
$I_D$	-30A



### Description

AP3P020 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance.

### Absolute Maximum Ratings @ $T_J=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C=25^\circ\text{C}$	Drain Current, $V_{GS}$ @ 10V	-30	A
$I_D @ T_C=100^\circ\text{C}$	Drain Current, $V_{GS}$ @ 10V	-18.5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-100	A
$P_D @ T_C=25^\circ\text{C}$	Total Power Dissipation	25	W
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	2	W
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	28.8	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	5	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>4</sup>	62.5	$^\circ\text{C}/\text{W}$



# AP3P020H

## Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A	-	-	20	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	-	-	40	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-	-3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-10A	-	18	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =-10A	-	12	19.2	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-15V	-	5	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	4	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =-15V	-	10	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =-15A	-	35	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =6Ω	-	40	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =-10V	-	46	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	1300	2080	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-15V	-	190	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	135	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	8	16	Ω

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =-15A, V <sub>GS</sub> =0V	-	-	-1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =-15A, V <sub>GS</sub> =0V,	-	11	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	4	-	nC

### Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=-30V , L=0.1mH , R<sub>G</sub>=25Ω , V<sub>GS</sub>=-10V
- 4.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT, AUTOMOTIVE OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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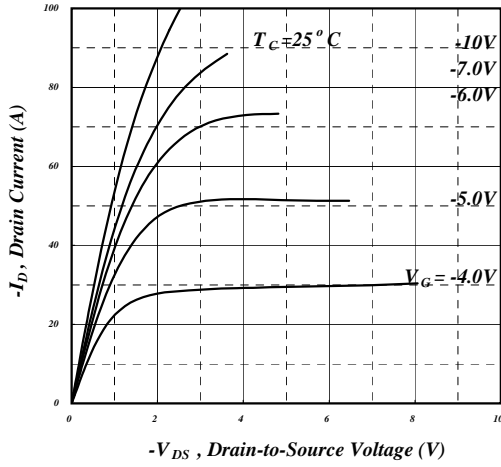


Fig 1. Typical Output Characteristics

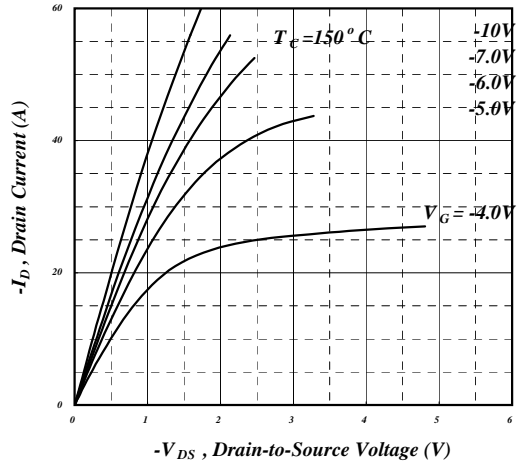


Fig 2. Typical Output Characteristics

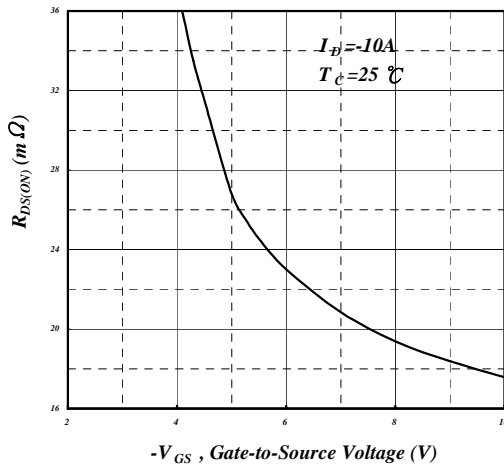


Fig 3. On-Resistance v.s. Gate Voltage

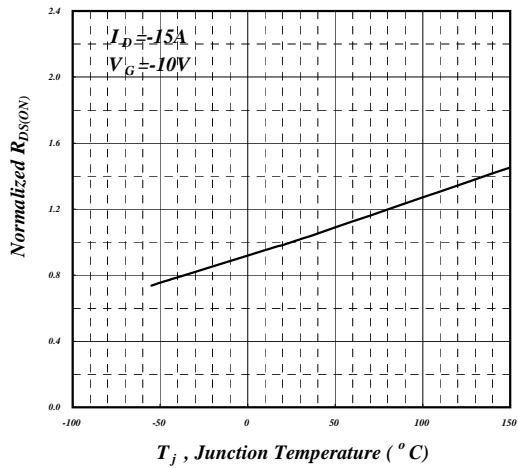


Fig 4. Normalized On-Resistance v.s. Junction Temperature

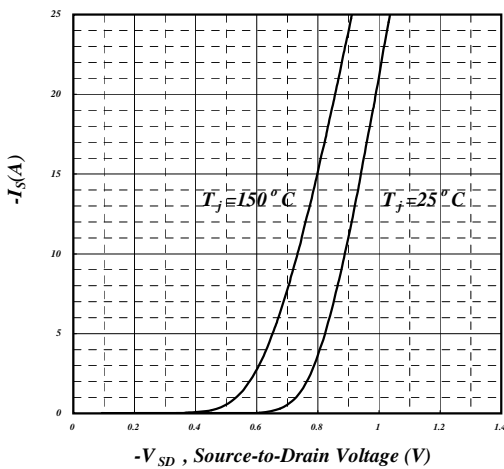


Fig 5. Forward Characteristic of Reverse Diode

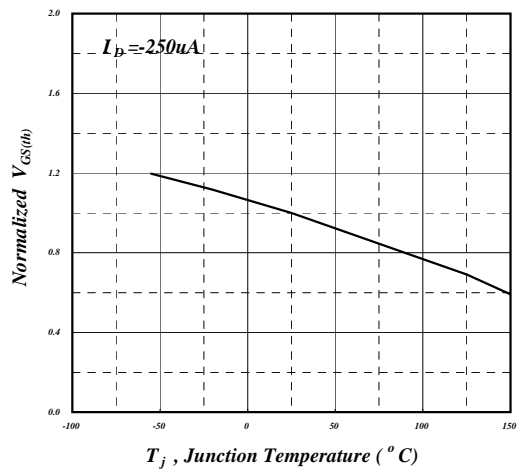
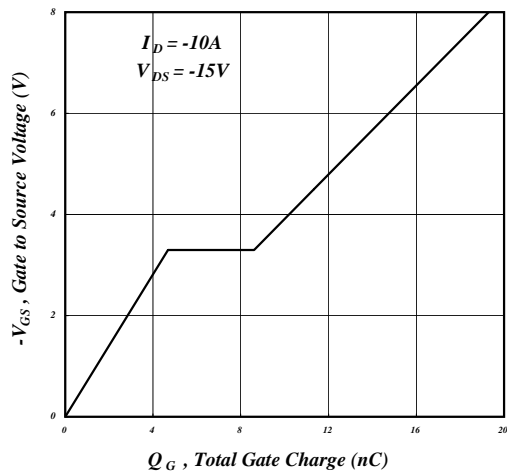
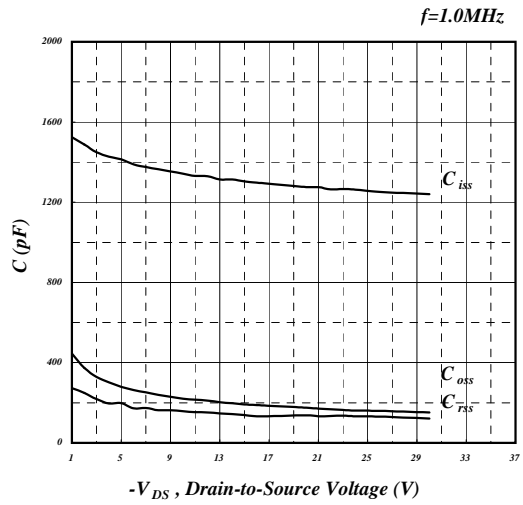


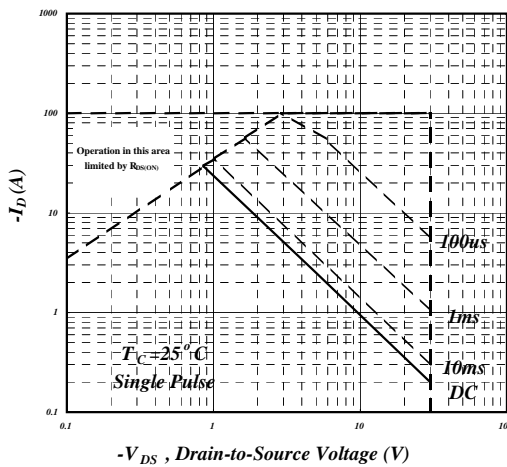
Fig 6. Gate Threshold Voltage v.s. Junction Temperature



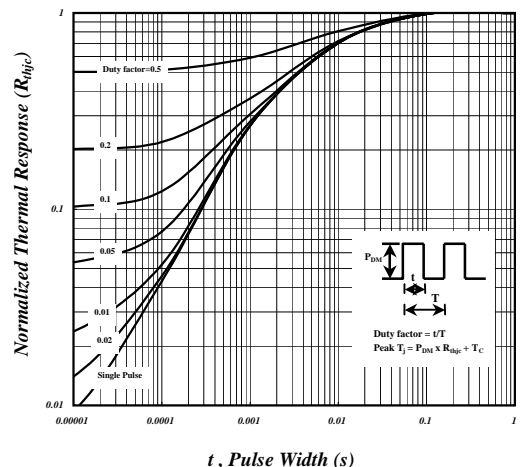
**Fig 7. Gate Charge Characteristics**



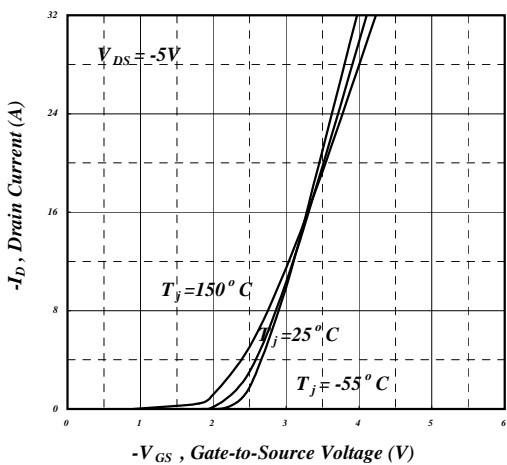
**Fig 8. Typical Capacitance Characteristics**



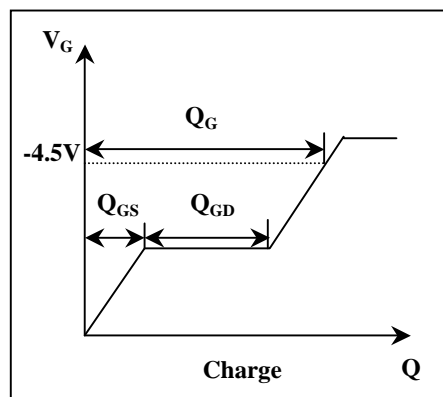
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Transfer Characteristics**



**Fig 12. Gate Charge Waveform**

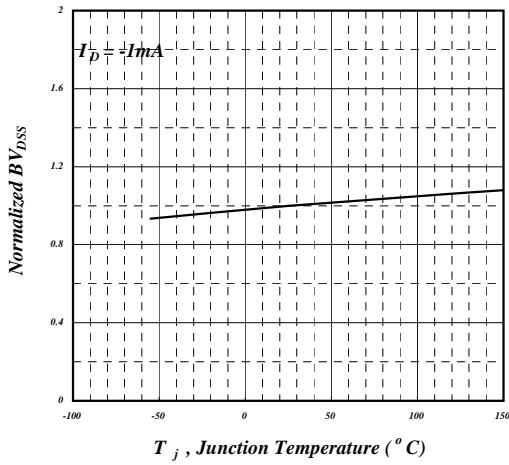


Fig 13. Normalized  $BV_{DSS}$  v.s. Junction Temperature

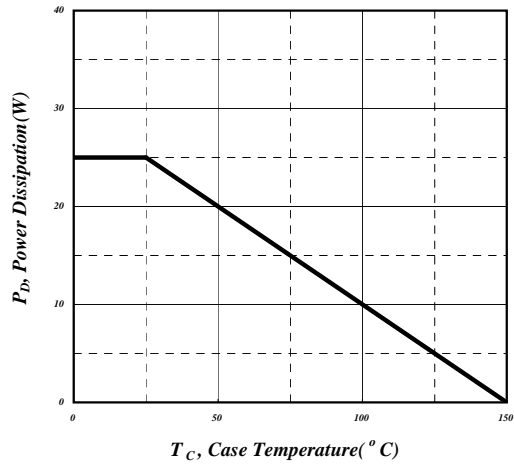


Fig 14. Total Power Dissipation

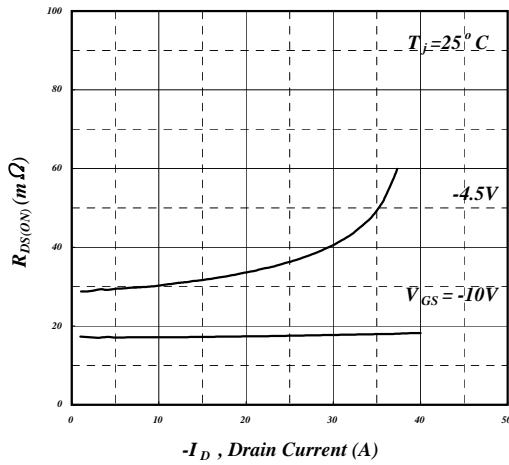


Fig 15. Typ. Drain-Source on State Resistance

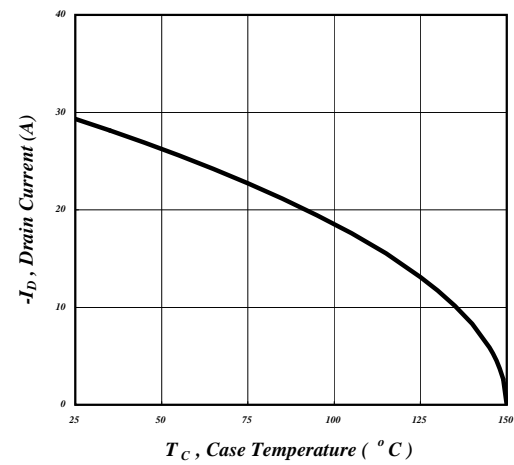


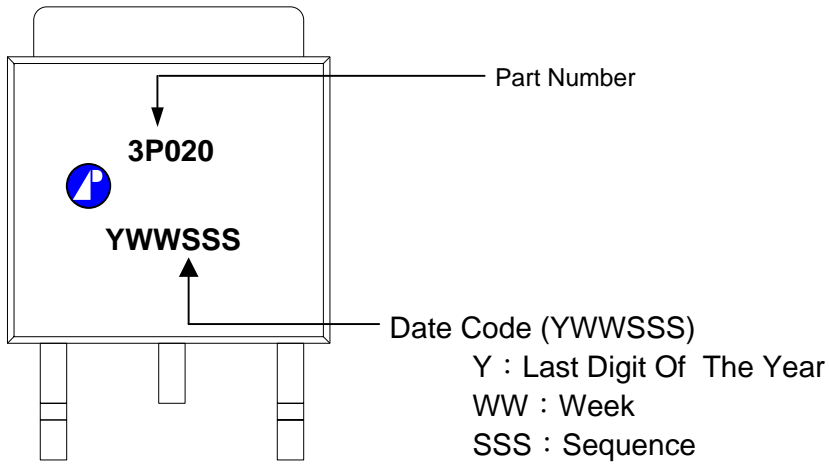
Fig 16. Drain Current v.s. Case Temperature



# AP3P020H

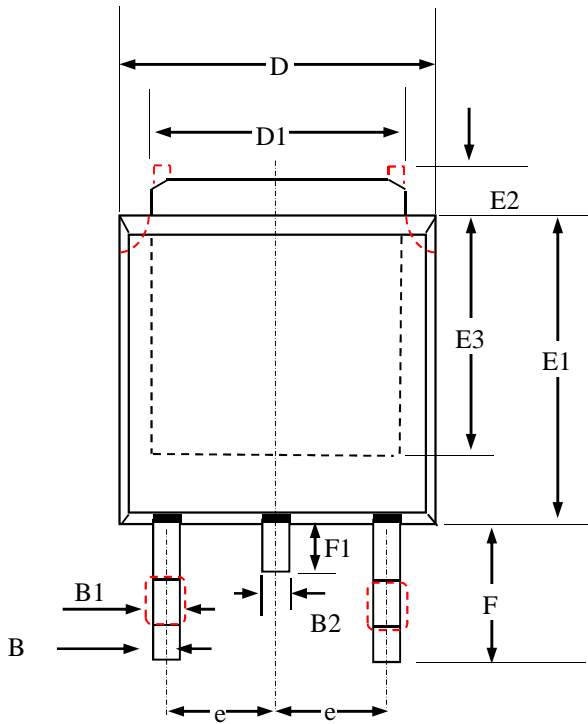
## MARKING INFORMATION

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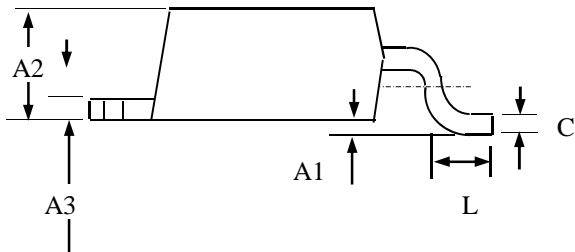




## Package Outline : TO-252



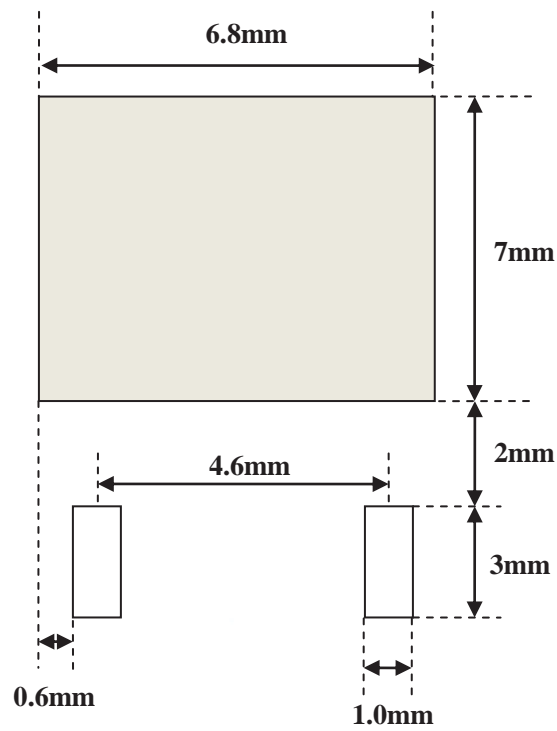
SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	2.18	2.30	2.40
A3	0.40	0.50	0.65
B	0.40	0.70	1.00
B1	0.50	0.85	1.20
D	6.00	6.50	6.80
D1	4.80	5.35	5.90
E3	4.00 (ref.)		
F	2.00	2.63	3.05
F1	0.50	0.85	1.20
E1	5.00	5.70	6.30
E2	0.50	1.10	1.80
e	2.3 (ref)		
C	0.35	0.525	0.70
A1	0.00	—	0.25
B2	—	—	1.25
L	0.90	1.34	1.78



- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.
3. Thermal PAD, Body and Pin contour is for reference, it may has little difference by option.



**TO-252 FOOTPRINT :**





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